TECHNICAL DATA DATASHEET 4312, REV C

STANDARD RECOVERY SILICON RECTIFIER DIE

Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Glass Passivated Epitaxial Diode with Mesa Structure
- Soft Reverse Recovery at Low and High Temperature
- Low Forward Voltage Drop and Low Reverse Current
- Electrically and Mechanically Stable during and after Packaging

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-		V
1C5550			200	
1C5551			400	
1C5552			600	
1C5553			800	
1C5554			1000	
Max. Output Current	Io	50% duty cycle, rectangular wave form; T _A = 55 °C	3.0	Α
Max. Peak One Cycle Non-	I _{FSM}	8.3 ms, sine pulse (1)	100	Α
Repetitive Surge Current				
Max. Junction Temperature	T_J	-	-55 to +175	°C
Max. Storage Temperature	T _{stg}	-	-55 to +200	°C
Reverse Recovery Time	t _{rr}	I _F =0.5A, I _R =1.0A, I _{RM} =0.25A	2.0	μS

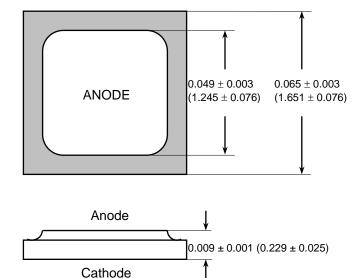
Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	9A, pulse, T _J = 25 °C		V
1C5550			1.2	
1C5551			1.2	
1C5552			1.2	
1C5553			1.3	
1C5554			1.3	
Max. Reverse Current	I _{R1}	$V_R = V_{RWM}$, pulse, $T_J = 25$ °C	1.0	μΑ
70	I _{R2}	$V_R = V_{RWM}$, pulse, $T_J = 125 ^{\circ}C$	60	μΑ

⁽¹⁾ in TO package

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Dimensions in inches (mm):

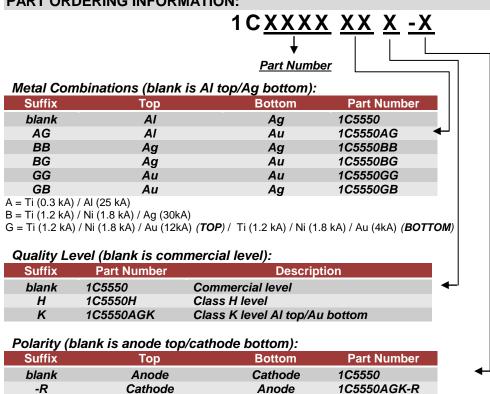


Bottom side metalization: Ti/Ni/Ag - 30 kÅ nominal

Top side metalization: AI - 25 kÅ minimum

Bottom side is cathode, top side is anode.





SENSITRON

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